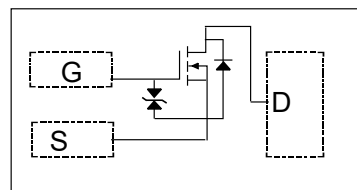


Description

PNM3FD703E0-2 is designed for high speed switching applications

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary			
$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$V_{GS(th)}(V)$	$I_D(A)$
40	7.5@ $V_{GS}=10V$	0.5 to 1.5	0.18

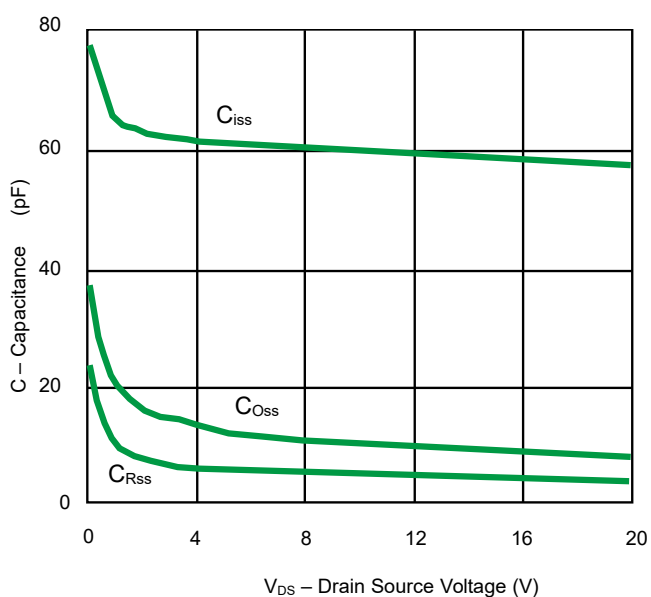
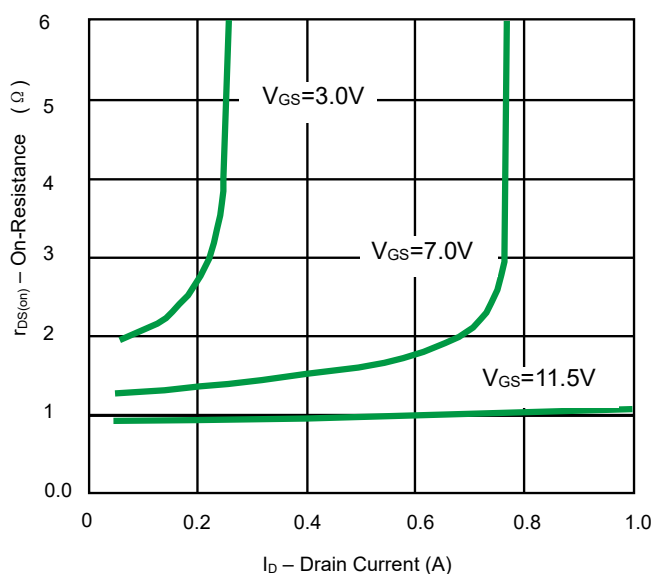
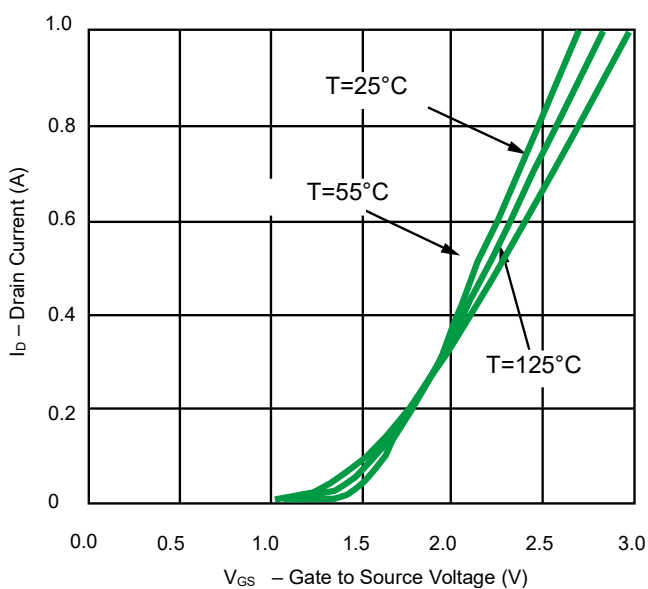
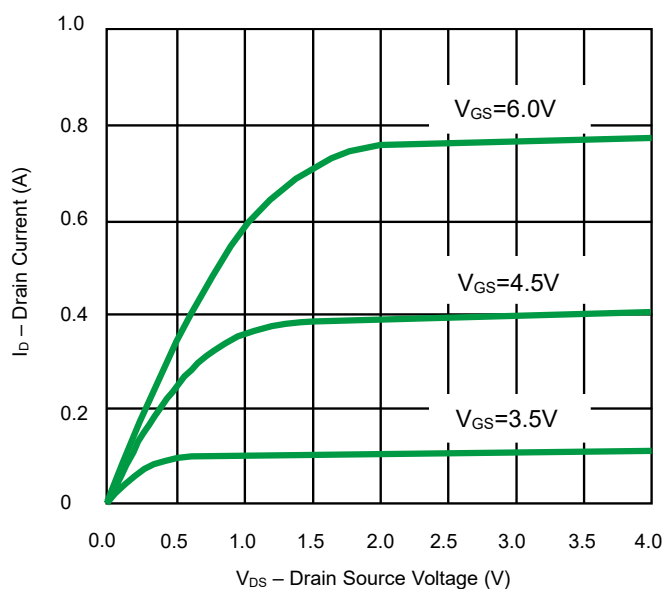


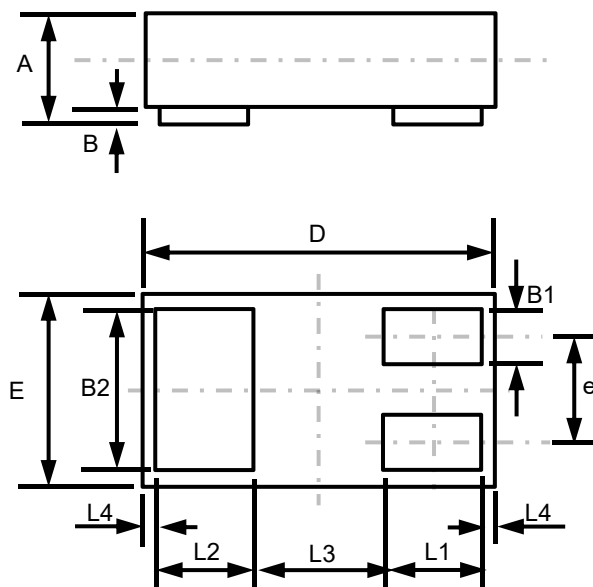
Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V _{DSS}	I _D =10μA, V _{GS} =0V	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	0.5	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	-	1.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =5V, I _D =0.05A	-	-	7.5	Ω
		V _{GS} =10V, I _D =0.5A	-	-	7.5	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	-	40	pF
Output Capacitance	C _{DSS}		-	-	20	pF
Reverse Transfer Capacitance	C _{RSS}		-	-	5	pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DS} =30V, V _{GS} =10V, R _G =25Ω, R _L =150Ω I _D =0.2A	-	-	20	ns
Turn-Off Delay Time	t _{d(off)}		-	-	20	ns

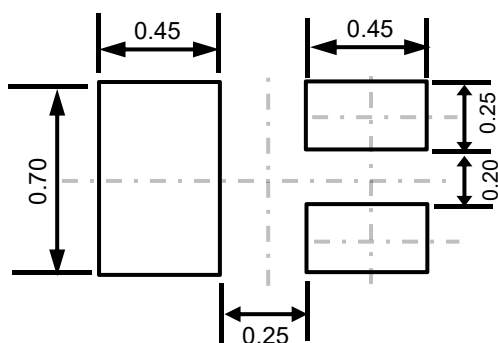
Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	0.18	A
	Pulsed	I_D	0.36	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	150	mW

Typical Characteristics


Product dimension (DFN1006-3L)


Dim	Millimeters		
	MIN	Typ	MAX
A	0.33	0.47	0.50
B	0.00	0.03	0.05
B1	0.10	0.15	0.20
B2	0.45	0.50	0.55
D	0.85	1.00	1.15
E	0.45	0.60	0.75
e	--	0.35	--
L1	0.20	0.25	0.30
L2	0.20	0.25	0.30
L3	--	0.39	--
L4	--	0.05	--


Suggested PCB Layout

Unit:mm

Device	Package	Reel	Shipping
PNM3FD703E0-2	DFN1006-3L(Pb-Free)	7"	10000 / Tape & Reel